IN THE CLAIMS:

(1) Please cancel Claims 1-10, without prejudice or disclaimer.

(2) Please add the following new Claims 44-53:

44. A semiconductor device, comprising:

a lateral metal-oxide semiconductor field effect transistor (MOSFET), including:

a silicon carbide tub located within or contacting a conductive substrate including a material different from the silicon carbide tub;

a gate formed on the silicon carbide tub; and

source and drain regions located in the silicon carbide tub and laterally offset from

the gate; and

complimentary metal-oxide semiconductor (CMOS) device formed on the conductive substrate, the CMOS device having a tub comprising the material.

- 45. The semiconductor device as recited in Claim 44 wherein the MOSFET has a breakdown voltage greater than an operating voltage of the CMOS device.
- 46. The semiconductor device as recited in Claim 44 wherein the MOSFET has a breakdown voltage of at least about 10 volts and the CMOS device has a breakdown voltage between about 3 volts and 5 volts.
- 47. The semiconductor device as recited in Claim 44 wherein the semiconductor device is a power converter and the MOSFET is a power switch for the power converter.

48. The remissional action device as recited in Claim 44 wherein the silicon carbide tub is located within a trench formed in the conductive substrate.



- The semiconductor device as recited in Claim 44 wherein the silicon carbide tub is located over the conductive substrate.
- 50. The semiconductor device as recited in Claim 44 wherein the material is doped silicon, wherein the silicon is doped with a p-type dopant or an n-type dopant.
- 51. The semiconductor device as recited in Claim 44 wherein the source and drain regions are doped with a p-type dopant or an n-type dopant.
- 52. The semiconductor device as recited in Claim 44 further comprising a buried oxide layer formed in the conductive substrate.
- 53. The semiconductor device as recited in Claim 44 wherein the conductive substrate comprises silicon and wherein the silicon carbide tub comprises a 3C silicon carbide.